

Abstract of the Disclosure:

A semiconductor configuration has a base layer made of semiconductor material and formed, in particular, by a substrate. An insulation layer is arranged above the base layer, and a layer made of monocrystalline silicon adjoins the insulation layer. A passivating substance is present, with the formation of Si-X bonds, in the region of the interface between the insulation layer and the monocrystalline silicon layer. The bond energy of the Si-X bond is greater than the bond energy of an Si-H bond.

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